

ABSTRACT OF THE DISCLOSURE

A semiconductor light receiving device is disclosed which is capable of receiving a first wavelength band light beam and a second wavelength band light beam having a shorter wavelength than that of the first wavelength band light beam. The device has a light absorbing layer of a first conductivity type formed on a semiconductor surface region of the semiconductor substrate. the light absorbing layer absorbs the first and second wavelength band light beams. A cap layer of the first conductivity type is formed on the light absorbing layer. In the cap layer, a region of a second conductivity type is formed which transmits the second wavelength band light beam. A light collecting layer is formed on the semiconductor surface region and adjacently to the cap layer and the light absorbing layer. The light collecting layer has a convex shape with curvature to collect the second wavelength band light beam.